



# PMV250EPEA

40 V, P-channel Trench MOSFET

20 June 2014

Product data sheet

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- 1 kV ESD protected
- AEC-Q101 qualified

## 3. Applications

- Relay driver
- High-speed line driver
- High-side load switch
- Switching circuits

## 4. Quick reference data

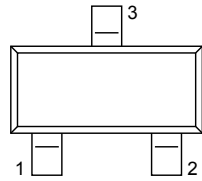
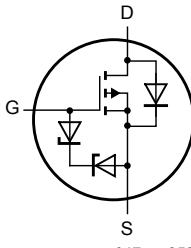
Table 1. Quick reference data

| Symbol                        | Parameter                        | Conditions                                                       | Min | Typ | Max  | Unit       |
|-------------------------------|----------------------------------|------------------------------------------------------------------|-----|-----|------|------------|
| $V_{DS}$                      | drain-source voltage             | $T_j = 25\text{ °C}$                                             | -   | -   | -40  | V          |
| $V_{GS}$                      | gate-source voltage              |                                                                  | -20 | -   | 20   | V          |
| $I_D$                         | drain current                    | $V_{GS} = -10\text{ V}; T_{amb} = 25\text{ °C}$                  | [1] | -   | -1.5 | A          |
| <b>Static characteristics</b> |                                  |                                                                  |     |     |      |            |
| $R_{DSon}$                    | drain-source on-state resistance | $V_{GS} = -10\text{ V}; I_D = -1.3\text{ A}; T_j = 25\text{ °C}$ | -   | 180 | 240  | m $\Omega$ |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline                                                                                        | Graphic symbol                                                                                       |
|-----|--------|-------------|-----------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------|
| 1   | G      | gate        |  <p>TO-236AB (SOT23)</p> |  <p>017aaa259</p> |
| 2   | S      | source      |                                                                                                           |                                                                                                      |
| 3   | D      | drain       |                                                                                                           |                                                                                                      |

## 6. Ordering information

Table 3. Ordering information

| Type number | Package  |                                          |         |
|-------------|----------|------------------------------------------|---------|
|             | Name     | Description                              | Version |
| PMV250EPEA  | TO-236AB | plastic surface-mounted package; 3 leads | SOT23   |

## 7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMV250EPEA  | %JY          |

[1] % = placeholder for manufacturing site code

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                    | Parameter                                    | Conditions                                                                       |     | Min | Max  | Unit |
|---------------------------|----------------------------------------------|----------------------------------------------------------------------------------|-----|-----|------|------|
| $V_{DS}$                  | drain-source voltage                         | $T_j = 25\text{ °C}$                                                             |     | -   | -40  | V    |
| $V_{GS}$                  | gate-source voltage                          |                                                                                  |     | -20 | 20   | V    |
| $I_D$                     | drain current                                | $V_{GS} = -10\text{ V}; T_{amb} = 25\text{ °C}$                                  | [1] | -   | -1.5 | A    |
|                           |                                              | $V_{GS} = -10\text{ V}; T_{amb} = 100\text{ °C}$                                 | [1] | -   | -1   | A    |
| $I_{DM}$                  | peak drain current                           | $T_{amb} = 25\text{ °C};$ single pulse; $t_p \leq 10\text{ }\mu\text{s}$         |     | -   | -6   | A    |
| $E_{DS(AL)S}$             | non-repetitive drain-source avalanche energy | $T_{j(init)} = 25\text{ °C}; I_D = -0.26\text{ A};$ DUT in avalanche (unclamped) |     | -   | 5.5  | mJ   |
| $P_{tot}$                 | total power dissipation                      | $T_{amb} = 25\text{ °C}$                                                         | [2] | -   | 480  | mW   |
|                           |                                              |                                                                                  | [1] | -   | 890  | mW   |
|                           |                                              | $T_{sp} = 25\text{ °C}$                                                          |     | -   | 6250 | mW   |
| $T_j$                     | junction temperature                         |                                                                                  |     | -55 | 150  | °C   |
| $T_{amb}$                 | ambient temperature                          |                                                                                  |     | -55 | 150  | °C   |
| $T_{stg}$                 | storage temperature                          |                                                                                  |     | -65 | 150  | °C   |
| <b>Source-drain diode</b> |                                              |                                                                                  |     |     |      |      |
| $I_S$                     | source current                               | $T_{amb} = 25\text{ °C}$                                                         | [1] | -   | -0.9 | A    |
| <b>ESD maximum rating</b> |                                              |                                                                                  |     |     |      |      |
| $V_{ESD}$                 | electrostatic discharge voltage              | HBM                                                                              | [3] | -   | 1000 | V    |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain  $6\text{ cm}^2$ .

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

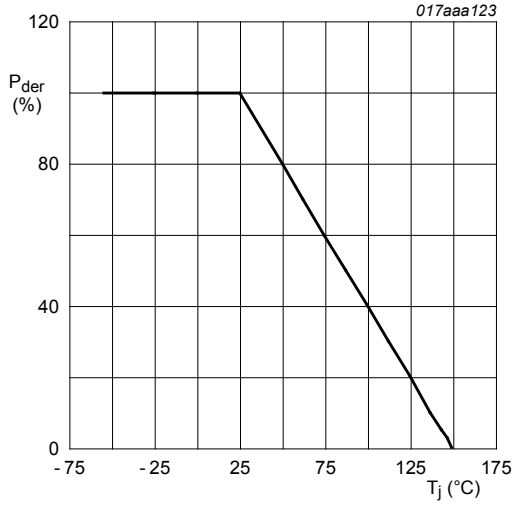


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100 \%$$

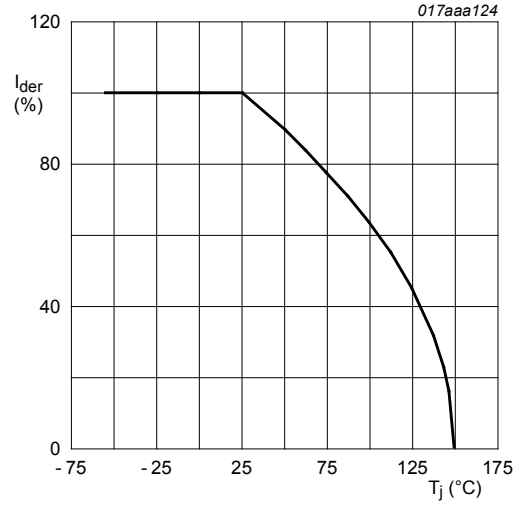
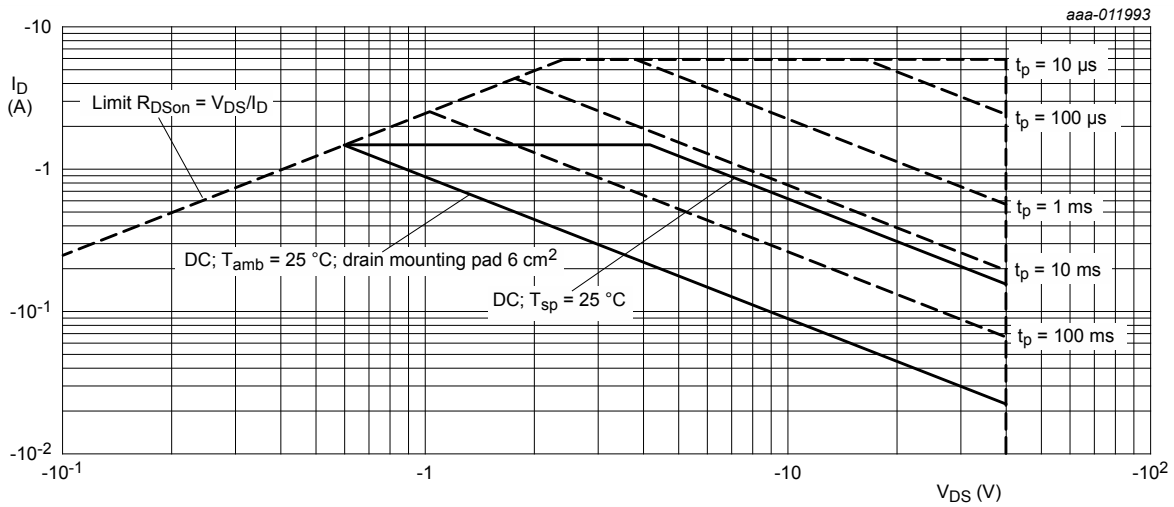


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100 \%$$



I<sub>DM</sub> = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

## 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol               | Parameter                                   | Conditions  |     | Min | Typ | Max | Unit |
|----------------------|---------------------------------------------|-------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient | in free air | [1] | -   | 230 | 260 | K/W  |
|                      |                                             |             | [2] | -   | 120 | 140 | K/W  |

| Symbol         | Parameter                                        | Conditions | Min | Typ | Max | Unit |
|----------------|--------------------------------------------------|------------|-----|-----|-----|------|
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point |            | -   | 15  | 20  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

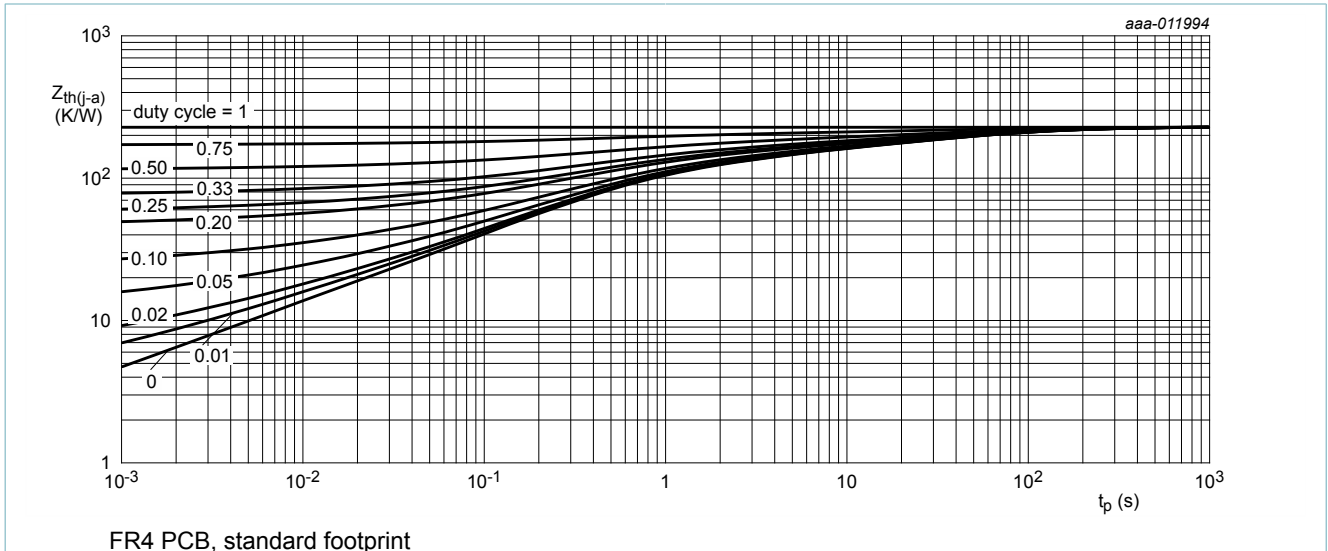


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

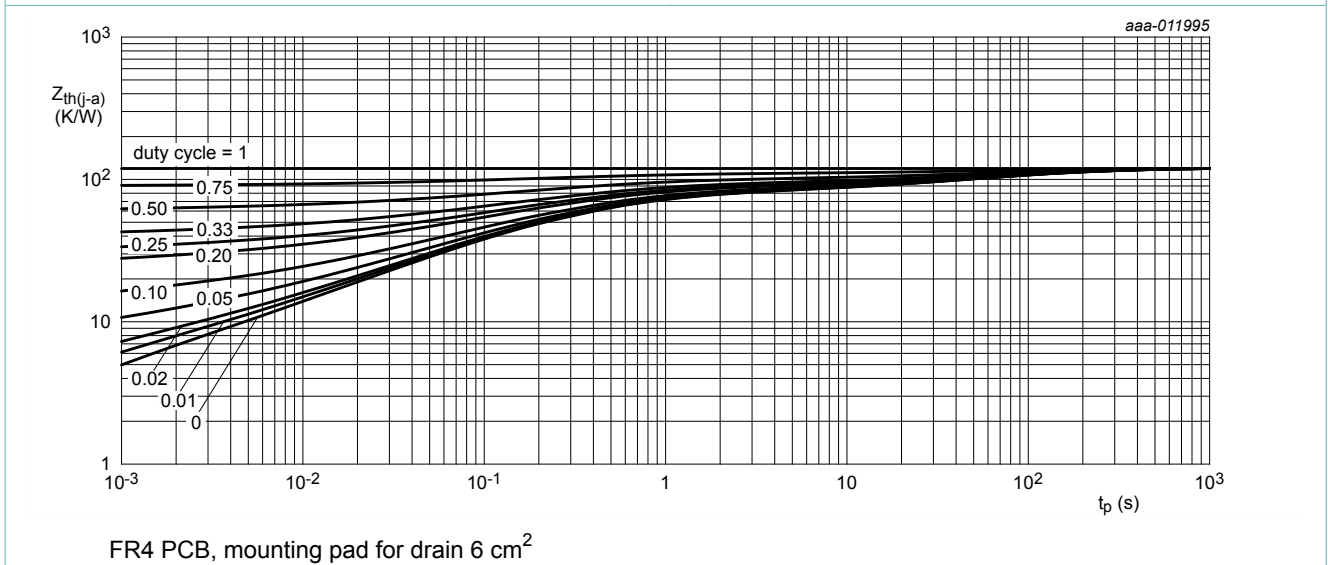
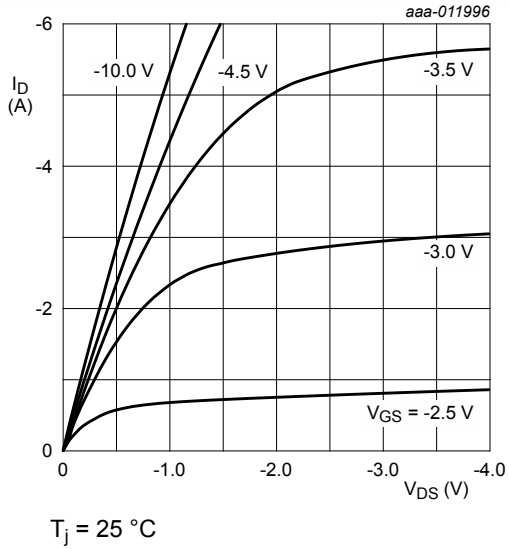


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

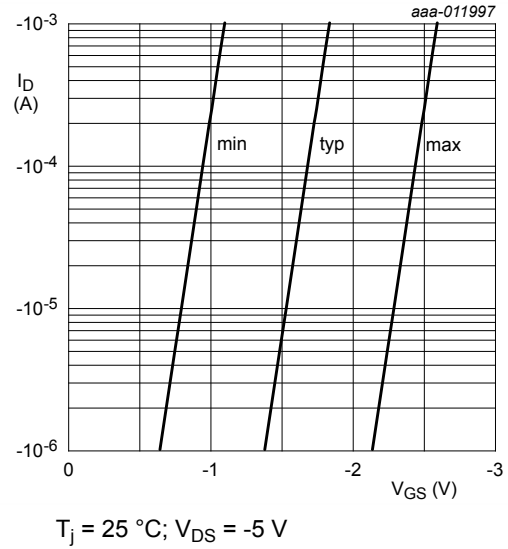
## 10. Characteristics

Table 7. Characteristics

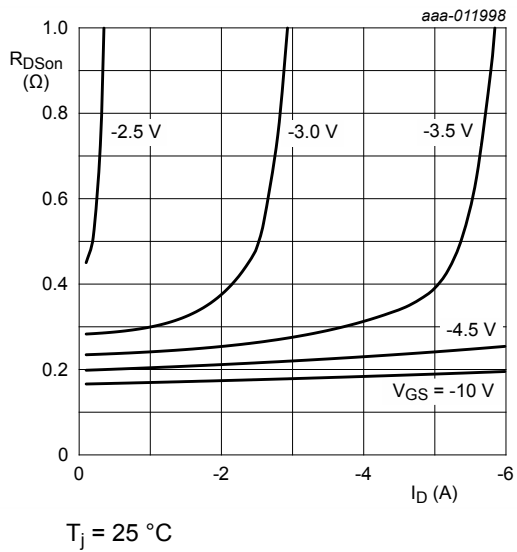
| Symbol                         | Parameter                        | Conditions                                                                                                       | Min | Typ  | Max  | Unit       |
|--------------------------------|----------------------------------|------------------------------------------------------------------------------------------------------------------|-----|------|------|------------|
| <b>Static characteristics</b>  |                                  |                                                                                                                  |     |      |      |            |
| $V_{(BR)DSS}$                  | drain-source breakdown voltage   | $I_D = -250 \mu A$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$                                                | -40 | -    | -    | V          |
| $V_{GSth}$                     | gate-source threshold voltage    | $I_D = -250 \mu A$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ }^\circ C$                                             | -1  | -1.7 | -2.5 | V          |
| $I_{DSS}$                      | drain leakage current            | $V_{DS} = -40 V$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$                                                  | -   | -    | -1   | $\mu A$    |
|                                |                                  | $V_{DS} = -40 V$ ; $V_{GS} = 0 V$ ; $T_j = 150 \text{ }^\circ C$                                                 | -   | -    | -20  | $\mu A$    |
| $I_{GSS}$                      | gate leakage current             | $V_{GS} = 20 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$                                                   | -   | -    | 10   | $\mu A$    |
|                                |                                  | $V_{GS} = -20 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$                                                  | -   | -    | -10  | $\mu A$    |
| $R_{DSon}$                     | drain-source on-state resistance | $V_{GS} = -10 V$ ; $I_D = -1.3 A$ ; $T_j = 25 \text{ }^\circ C$                                                  | -   | 180  | 240  | m $\Omega$ |
|                                |                                  | $V_{GS} = -10 V$ ; $I_D = -1.3 A$ ; $T_j = 150 \text{ }^\circ C$                                                 | -   | 300  | 400  | m $\Omega$ |
|                                |                                  | $V_{GS} = -4.5 V$ ; $I_D = -0.8 A$ ; $T_j = 25 \text{ }^\circ C$                                                 | -   | 220  | 300  | m $\Omega$ |
| $g_{fs}$                       | forward transconductance         | $V_{DS} = -5 V$ ; $I_D = -2 A$ ; $T_j = 25 \text{ }^\circ C$                                                     | -   | 4.5  | -    | S          |
| $R_G$                          | gate resistance                  | $f = 1 \text{ MHz}$                                                                                              | -   | 19   | -    | $\Omega$   |
| <b>Dynamic characteristics</b> |                                  |                                                                                                                  |     |      |      |            |
| $Q_{G(tot)}$                   | total gate charge                | $V_{DS} = -20 V$ ; $I_D = -1.3 A$ ; $V_{GS} = -10 V$ ;<br>$T_j = 25 \text{ }^\circ C$                            | -   | 4.7  | 6    | nC         |
| $Q_{GS}$                       | gate-source charge               |                                                                                                                  | -   | 0.8  | -    | nC         |
| $Q_{GD}$                       | gate-drain charge                |                                                                                                                  | -   | 0.7  | -    | nC         |
| $C_{iss}$                      | input capacitance                | $V_{DS} = -20 V$ ; $f = 1 \text{ MHz}$ ; $V_{GS} = 0 V$ ;<br>$T_j = 25 \text{ }^\circ C$                         | -   | 293  | 450  | pF         |
| $C_{oss}$                      | output capacitance               |                                                                                                                  | -   | 35   | -    | pF         |
| $C_{rss}$                      | reverse transfer capacitance     |                                                                                                                  | -   | 20   | -    | pF         |
| $t_{d(on)}$                    | turn-on delay time               | $V_{DS} = -20 V$ ; $I_D = -1.3 A$ ; $V_{GS} = -10 V$ ;<br>$R_{G(ext)} = 15 \Omega$ ; $T_j = 25 \text{ }^\circ C$ | -   | 4    | 6    | ns         |
| $t_r$                          | rise time                        |                                                                                                                  | -   | 6    | -    | ns         |
| $t_{d(off)}$                   | turn-off delay time              |                                                                                                                  | -   | 26   | 39   | ns         |
| $t_f$                          | fall time                        |                                                                                                                  | -   | 14   | -    | ns         |
| <b>Source-drain diode</b>      |                                  |                                                                                                                  |     |      |      |            |
| $V_{SD}$                       | source-drain voltage             | $I_S = -0.86 A$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$                                                   | -   | -0.8 | -1.2 | V          |



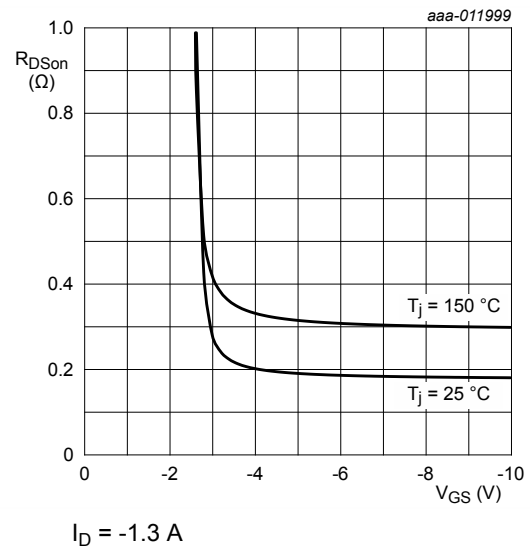
**Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values**



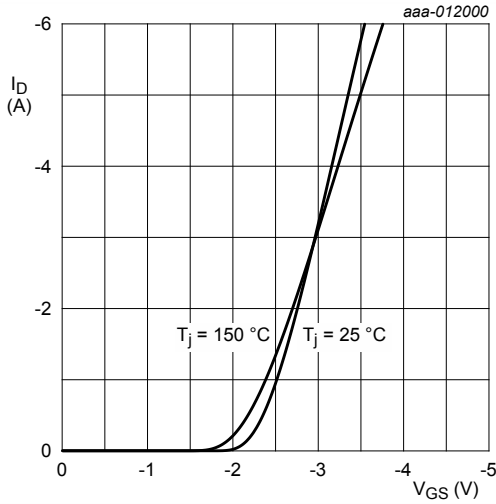
**Fig. 7. Sub-threshold drain current as a function of gate-source voltage**



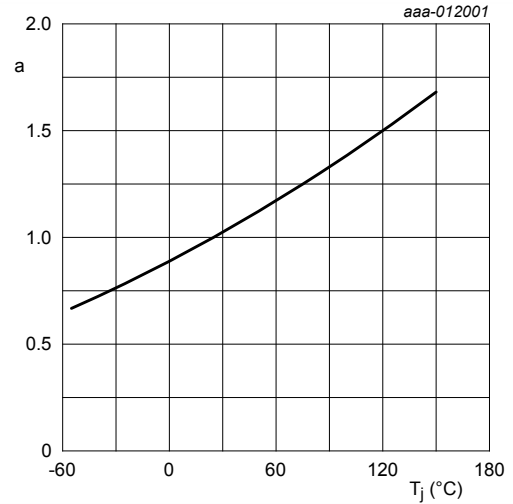
**Fig. 8. Drain-source on-state resistance as a function of drain current; typical values**



**Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values**

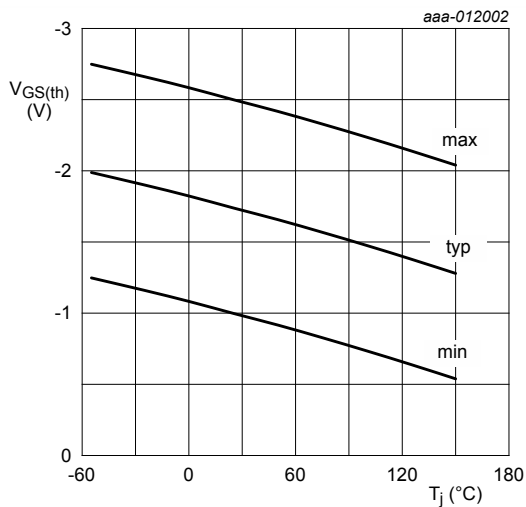


**Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



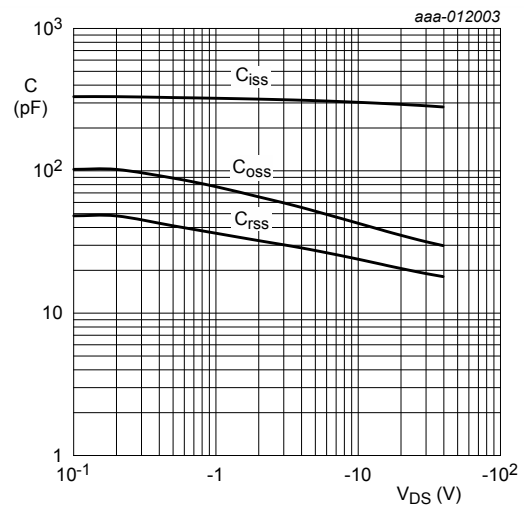
**Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values**

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$



**Fig. 12. Gate-source threshold voltage as a function of junction temperature**

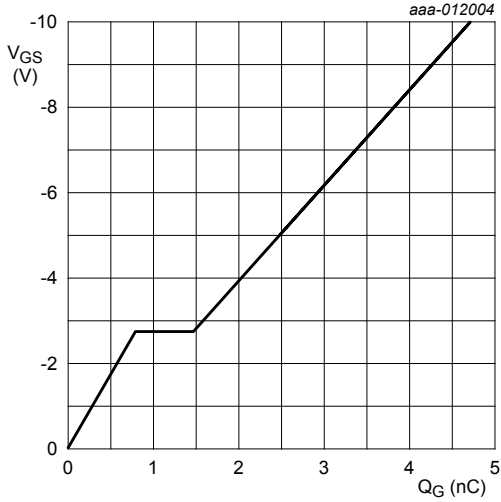
$I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$



**Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$





$I_D = -1.3 \text{ A}; V_{DS} = -20 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values

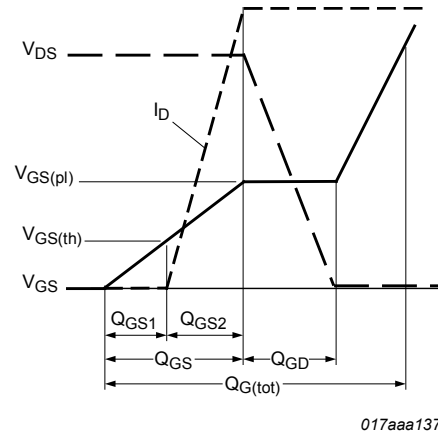
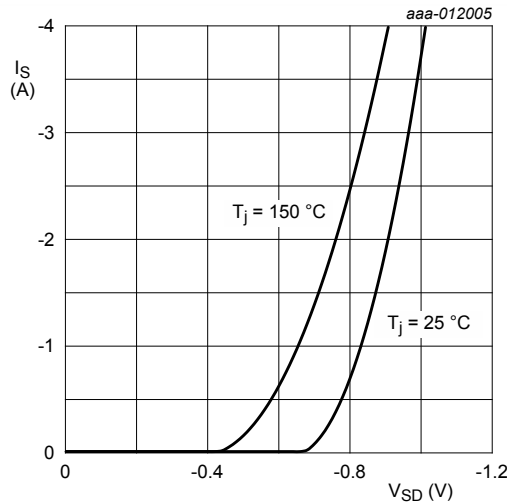


Fig. 15. MOSFET transistor: Gate charge waveform definitions



$V_{GS} = 0 \text{ V}$

Fig. 16. Source current as a function of source-drain voltage; typical values

### 11. Test information

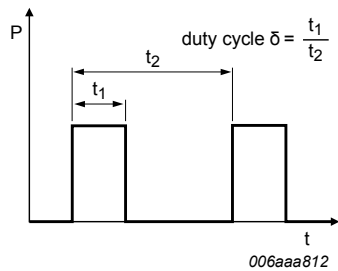


Fig. 17. Duty cycle definition

### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 12. Package outline

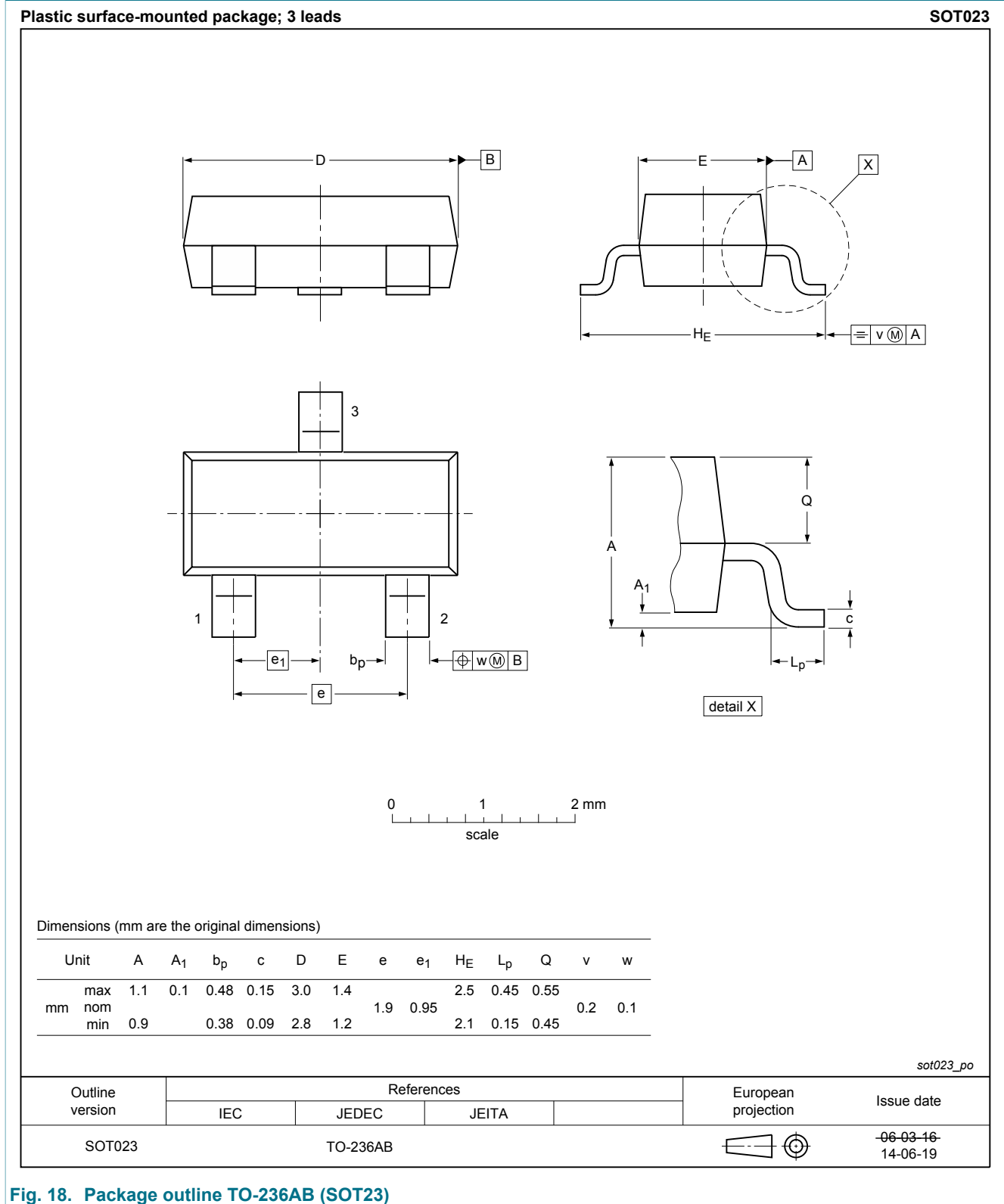


Fig. 18. Package outline TO-236AB (SOT23)

### 13. Soldering

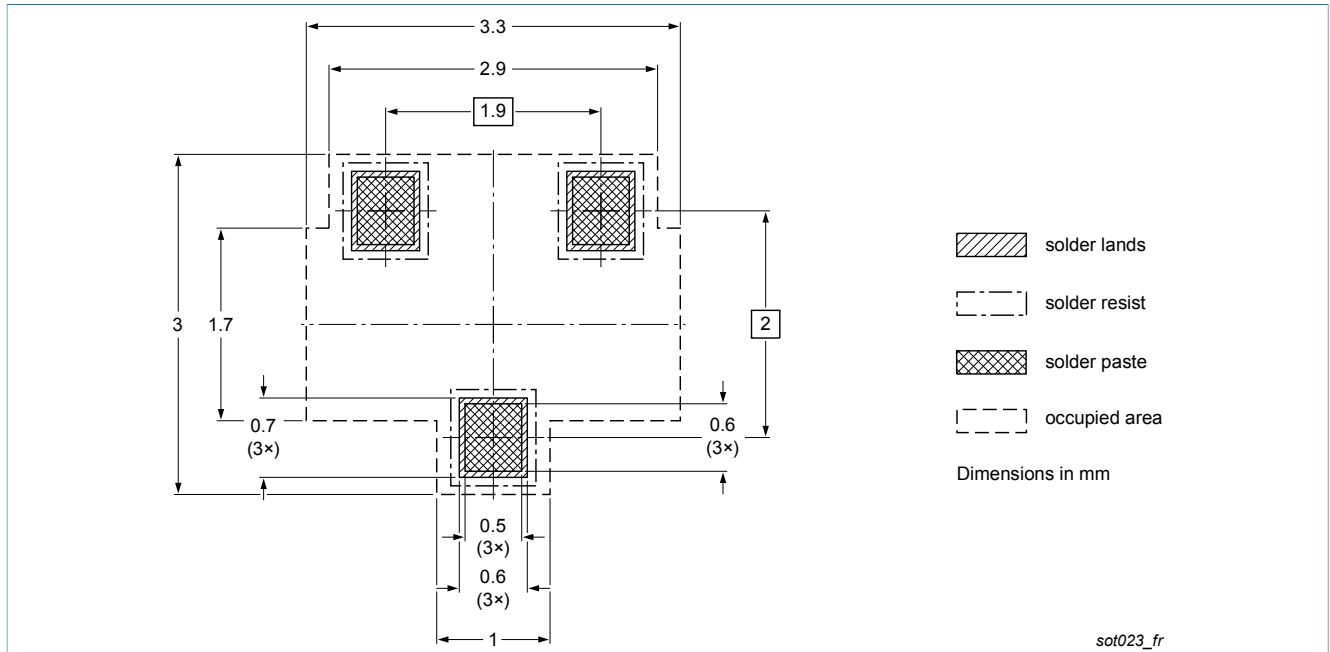


Fig. 19. Reflow soldering footprint for TO-236AB (SOT23)

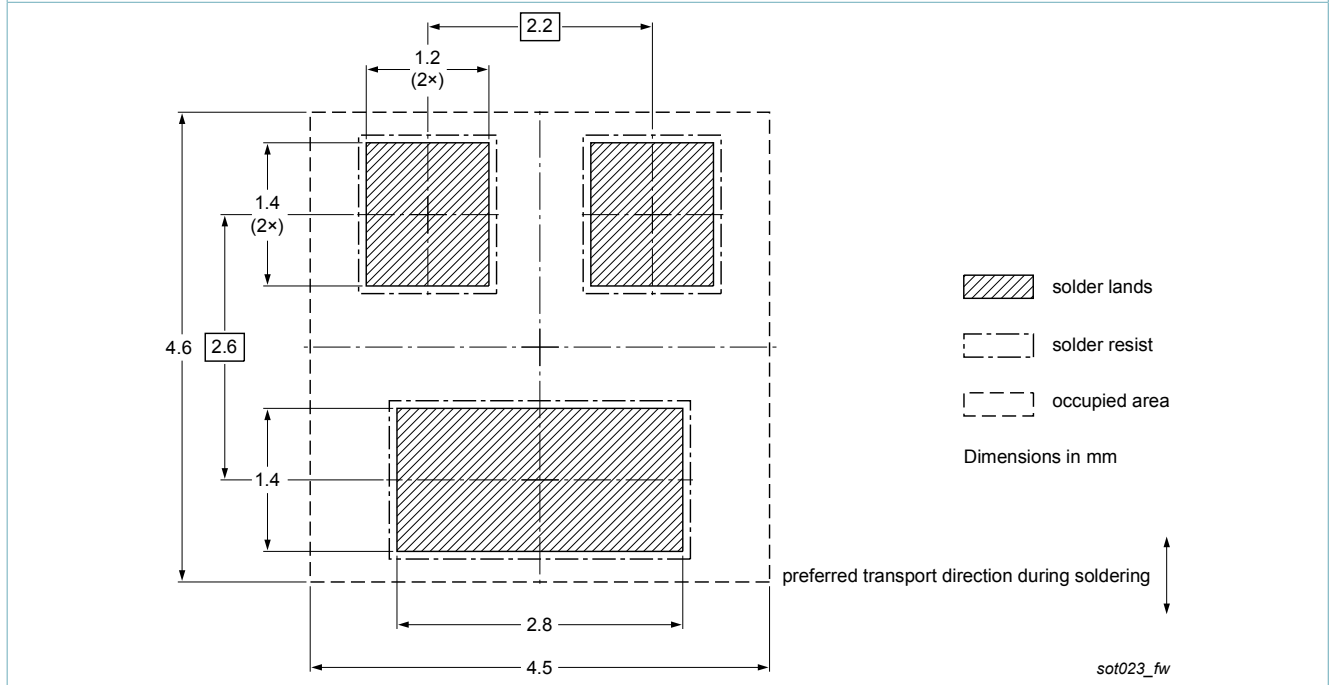


Fig. 20. Wave soldering footprint for TO-236AB (SOT23)

## 14. Revision history

Table 8. Revision history

| Data sheet ID                         | Release date | Data sheet status      | Change notice | Supersedes     |
|---------------------------------------|--------------|------------------------|---------------|----------------|
| PMV250EPEA v.3                        | 20140620     | Product data sheet     | -             | PMV250EPEA v.2 |
| Modification: Soldering chapter added |              |                        |               |                |
| PMV250EPEA v.2                        | 20140612     | Product data sheet     | -             | PMV250EPEA v.1 |
| PMV250EPEA v.1                        | 20140312     | Preliminary data sheet | -             | -              |

## 15. Legal information

### 15.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
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